

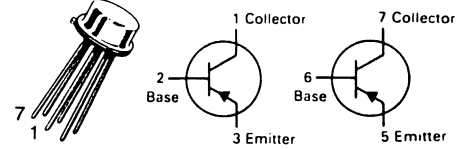


SOLID STATE INC.

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2N3806 thru 2N3810,A 2N3811,A



2N3810, 2N3811

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	500	600	mW
		2.86	3.43	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage(1) ($I_C = 10 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}, I_E = 0$) ($V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 150^\circ\text{C}$)	I_{CBO}	—	0.01 10	μAdc
Emitter Cutoff Current ($V_{BE} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	20	nAdc

ON CHARACTERISTICS

DC Current Gain(1) ($I_C = 1.0 \mu\text{Adc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3807,9,11,A	h_{FE}	75	—	—
($I_C = 10 \mu\text{Adc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3806,8,10,A 2N3807,9,11,A		100 225	—	—
($I_C = 100 \mu\text{Adc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	—
($I_C = 100 \mu\text{Adc}, V_{CE} = 5.0 \text{ Vdc}, T_A = -55^\circ\text{C}$)	2N3806,8,10,A 2N3807,9,11,A		75 150	—	—
($I_C = 500 \mu\text{Adc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	—
($I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	—
($I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	2N3806,8,10,A 2N3807,9,11,A		125 250	—	—
Collector-Emitter Saturation Voltage(1) ($I_C = 100 \mu\text{Adc}, I_B = 1.0 \mu\text{A}$) ($I_C = 1.0 \text{ mAdc}, I_B = 100 \mu\text{Adc}$)		$V_{CE(sat)}$	—	0.2 0.25	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 100 \mu\text{Adc}, I_B = 10 \mu\text{Adc}$) ($I_C = 1.0 \text{ mAdc}, I_B = 100 \mu\text{Adc}$)		$V_{BE(sat)}$	—	0.7 0.8	Vdc

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ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Base-Emitter On Voltage ($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(on)}$	—	0.7	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 500 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 30 \text{ MHz}$) ($I_C = 1.0 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	30 100	— 500	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{BE} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 100 \text{ kHz}$)	C_{ibo}	—	8.0	pF
Input Impedance ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	3.0 10	30 40	$k\Omega$
Voltage Feedback Ratio ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{re}	—	25	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	150 300	600 900	—
Output Admittance ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	5.0	60	μmhos
Noise Figure ($I_C = 100 \mu\text{A}$, $V_{CE} = 10 \text{ Vdc}$, $R_G = 3.0 \text{ kohms}$, $f = 100 \text{ Hz}$, $BW = 20 \text{ Hz}$)	NF	—	7.0 4.0	dB
Spot Noise $f = 1.0 \text{ kHz}$, $BW = 200 \text{ Hz}$		—	3.0 1.5	
$f = 10 \text{ kHz}$, $BW = 2.0 \text{ kHz}$		—	2.5 1.5	
Broadband Noise Bandwidth 10 Hz to 15.7 kHz		—	3.5 2.5	

MATCHING CHARACTERISTICS

DC Current Gain Ratio(2) ($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE1}/h_{FE2}	0.8 0.9 0.95	1.0 1.0 1.0	—
($I_C = 100 \mu\text{A}$, $V_{CE} = 50 \text{ Vdc}$, $T_A = -55$ to $+125^\circ\text{C}$)		0.85	1.0	
Base-Emitter Voltage Differential ($I_C = 10 \mu\text{A}$ to 10 mA , $V_{CE} = 5.0 \text{ Vdc}$)	$ V_{BE1} - V_{BE2} $	—	8.0 5.0	mVdc
($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$)		—	5.0 3.0 1.5	
Base-Emitter Voltage Differential Change Due to Temperature ($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$, $T_A = -55$ to $+25^\circ\text{C}$)	$\Delta(V_{BE1} - V_{BE2})$	—	1.6 0.8 0.4	mVdc
($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$, $T_A = +25$ to $+125^\circ\text{C}$)		—	2.0 1.0 0.5	

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

(2) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

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FIGURE 1 — DC CURRENT GAIN versus COLLECTOR CURRENT

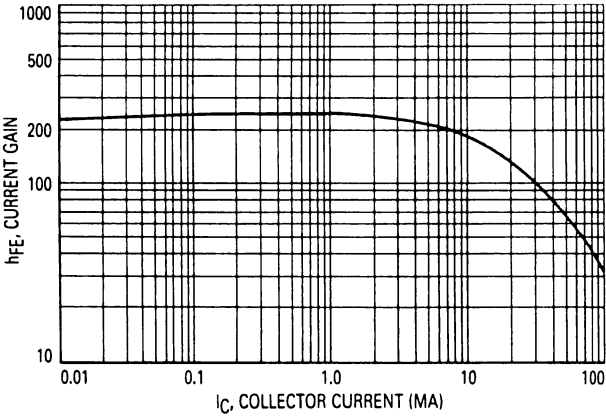


FIGURE 2 — DC CURRENT GAIN versus COLLECTOR CURRENT

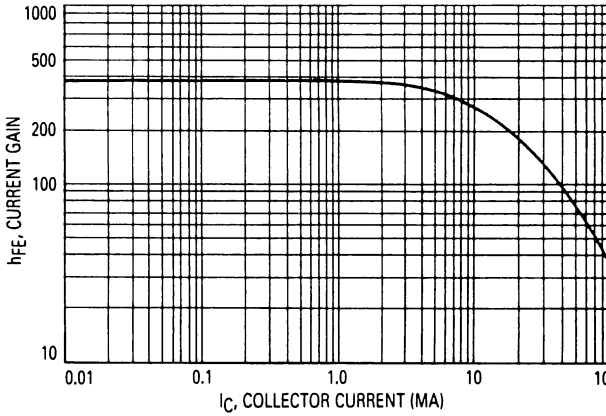


FIGURE 3 — "ON" VOLTAGES

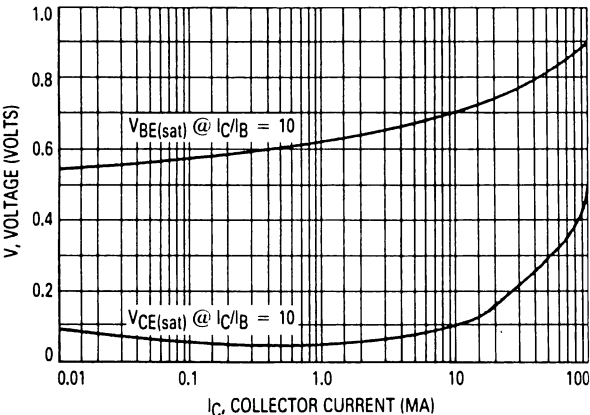
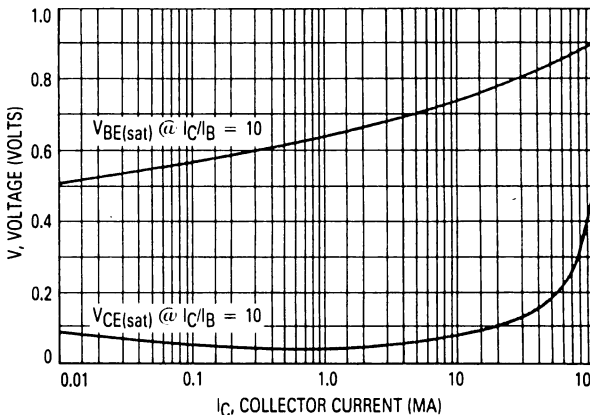
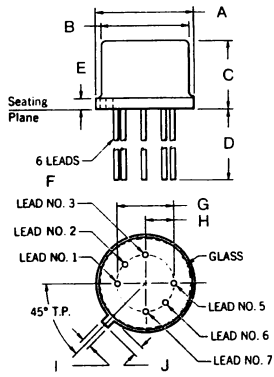


FIGURE 4 — "ON" VOLTAGES



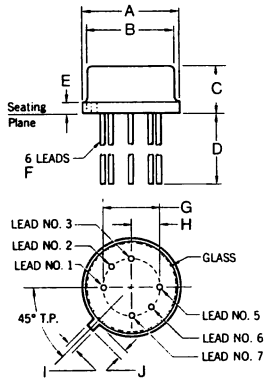
PHYSICAL DIMENSIONS

JEDEC (TO-77) outline



DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	.335		.370	8.51		9.39
B	.305		.335	7.75		8.51
C	.240		.260	6.10		6.60
D	.500			12.70		
E			.040			0.916
F	.016		.019	0.406		0.483
G		.200			5.08	
H		.100			2.54	
I	.028		.034	0.711		0.864
J	.029		.045	0.737		1.14

JEDEC (TO-78) outline



DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	.335		.370	8.51		9.39
B	.305		.335	7.75		8.51
C	.165		.185	4.19		4.69
D	.500			12.70		
E			.040			0.916
F	.016		.019	0.406		0.483
G		.200			5.08	
H		.100			2.54	
I	.028		.034	0.711		0.864
J	.029		.045	0.737		1.14